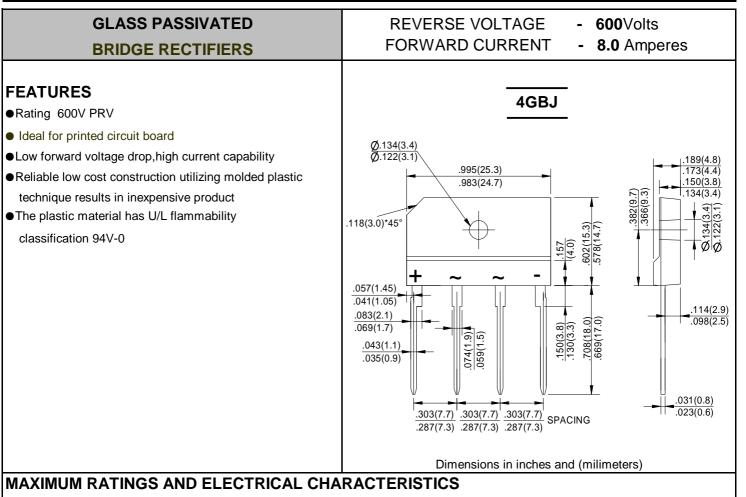


4GBJ806F



Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave ,60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

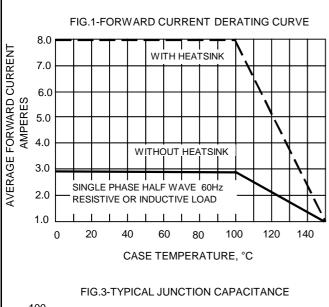
CHARACTERISTICS	SYMBOL	4GBJ806F	UNIT
Maximum Recurrent Peak Reverse Voltage	Vrrm	600	V
Maximum RMS Voltage	Vrms	420	V
Maximum DC Blocking Voltage	VDC	600	V
Maximum Average Forward (with heatsink Note 2) Rectified Current @ Tc=100°C (without heatsink)	l(AV)	8.0 2.9	A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load (JEDEC Method)	IFSM	160	А
Maximum Forward Voltage at 4.0A DC	Vf	0.95	V
Maximum DC Reverse Current@ TJ=25°Cat Rated DC Blocking Voltage@ TJ=125°C	IR	10.0 500	μΑ
I ² t Rating for Fusing (t<8.3ms)	l ² t	120	A ² s
Typical Junction Capacitance Per Element (Note1)	CJ	55	pF
Operating Temperature Range	TJ	-55 to +150	°C
Storage Temperature Range	Тѕтс	-55 to +150	°C

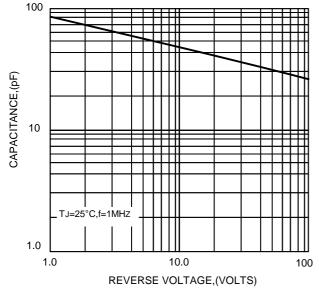
NOTES: 1.Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2.Device mounted on 75mm*75mm*1.6mm Cu plate heatsink.

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RATING AND CHARACTERTIC CURVES 4GBJ806F





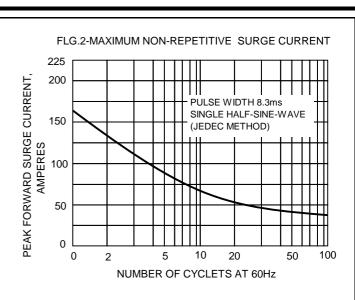
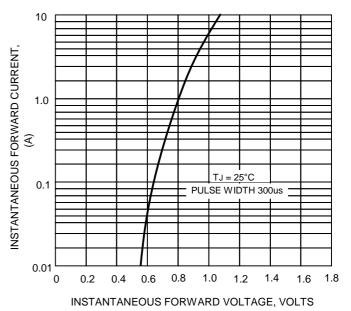
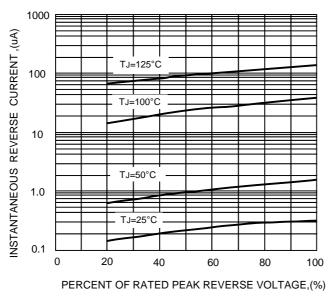


FIG.4-TYPICAL FORWARD CHARACTERISTICS







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